Abstract and Specification

Please replace the present Abstract of the Disclosure with the new Abstract of the Disclosure submitted herewith on a separate page.

Please replace paragraph [0065] with the following amended paragraph:

[0065] ~~Depending on the structure of the CVD apparatus, there may occur a phenomenon in which a film is grown at a dead zone region corresponding to an edge portion of the upper surface of the wafer, or at the lower surface of the wafer, and the grown film at the edge portion or lower surface of the wafer has a thickness different from that of the film formed on the upper surface of the wafer. In order to prevent the film from growing on the lower surface, a flow of N_2 gas is generally applied to the lower surface of the wafer during the deposition process. However, such a preventive measure is not feasible for application at the upper surface of the wafer considering the structure of the CVD apparatus, and thus a film of non-uniform thickness is usually deposited at a dead zone region of the upper surface of the wafer.~~

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The conventional CVD apparatus excepting the LPCVD apparatus usually deposits a film only on the front surface of the wafer. However, the film is also deposited on an upper sidewall of the wafer and on a rear surface of the wafer with different thickness from each other when using the conventional CVD apparatus due to structural restrictions of the CVD apparatus. Applying a flow of N2 gas to the rear surface of the wafer during the deposition process can prevent the film from depositing on the rear surface of the wafer. However, the film is necessarily deposited on the upper sidewall of the wafer due to the structure of the CVD apparatus, and thus a film of non-uniform thickness is usually deposited on the upper sidewall of the wafer.

Please replace paragraph [0070] with the following amended paragraph: